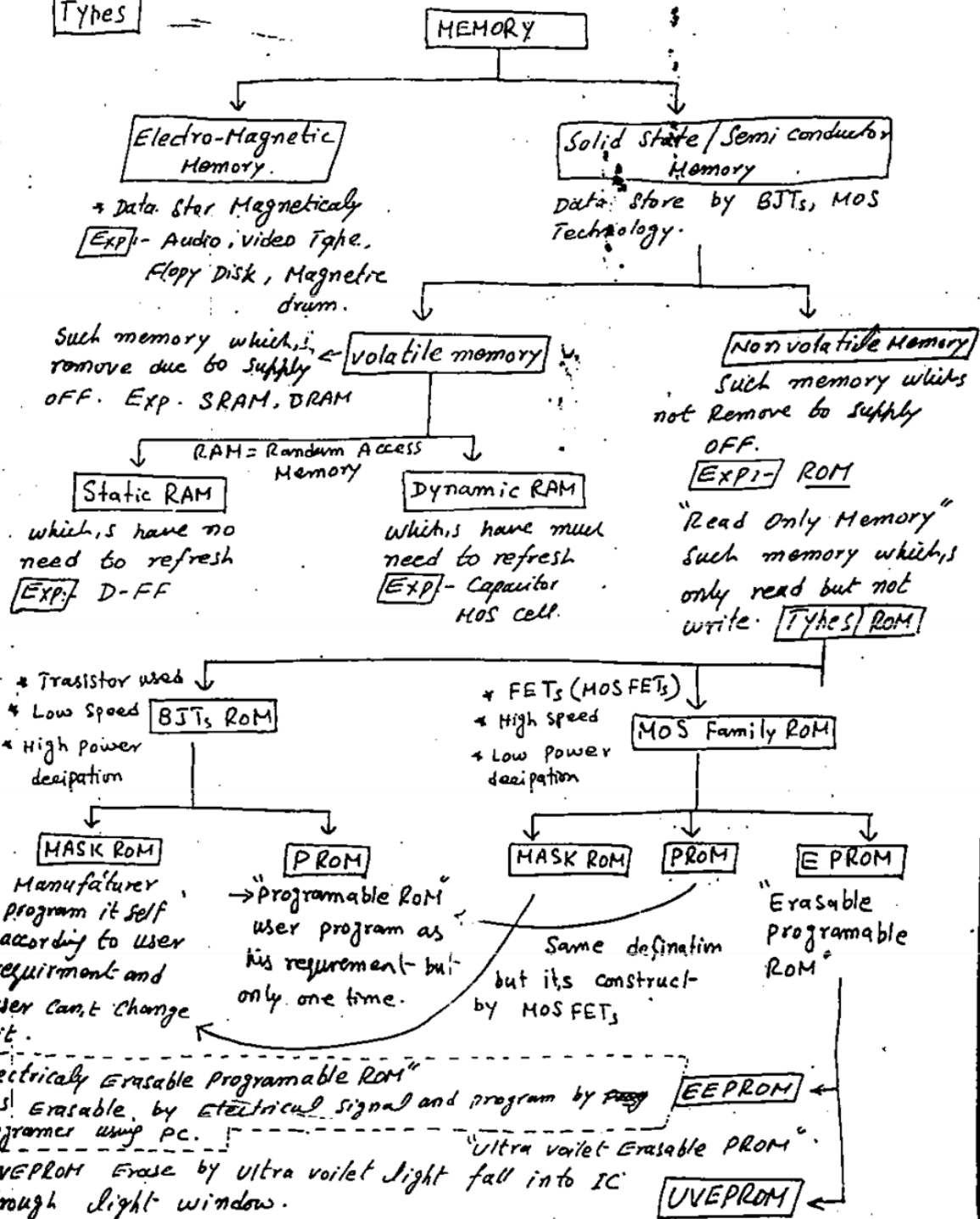


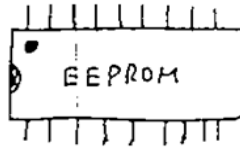
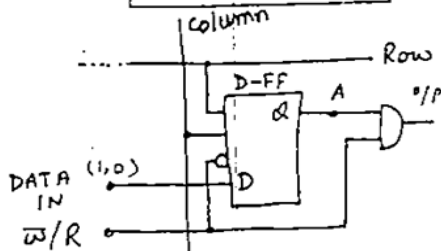
# CH 10 Memories:- 1/13

**Memory** Such device which, store the Digital Information/ Binary data are called memory.

**Types**

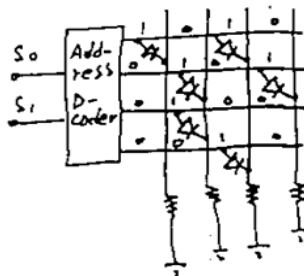
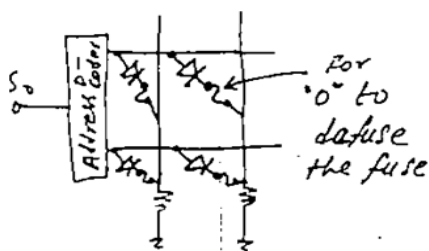
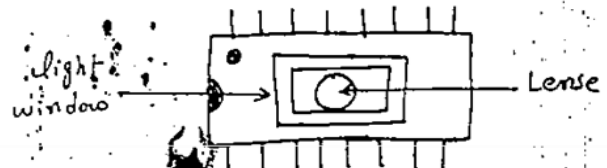
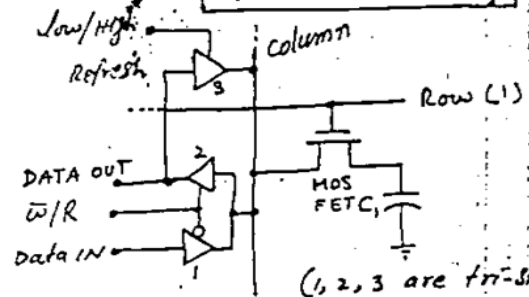


2/13

**EEPROM**Example:  $\mu$ -Controller**STATIC RAM cell**

\* **Write** 1st apply  $\bar{w}/R = 0$  then apply 1,0 at DATA IN & that 1,0 data appear at point "A" and will store their till supply OFF.

\* **Read** only apply 1 at  $\bar{w}/R$  data of point "A" will receive at o/p. 1,0.

**ROM programming****PROM****UVEPROM**Exp used in  $\mu$ -processor**Dynamic RAM cell**

(1, 2, 3 are tri-state)

\* **Write** DATA IN = 0,1,  $\bar{w}/R = 0$

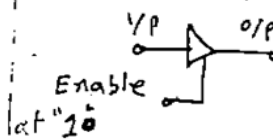
Tri-state 1 = ON, Row = 1, MOS = ON. data 0,1 appear at C<sub>1</sub> through column

\* **Read** only  $\bar{w}/R = 1$  Tri-state 2 = ON. Tri-state 1 = OFF. Data 0,1 appear at data OUT.

\* **Refresh** during **Read** Tri-State 3 = ON or High and 1,0 appear at C<sub>1</sub> through Tri-state 3.

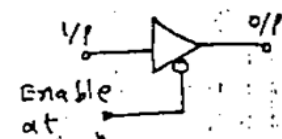
**TRI-STATE**

Active High



Yp	Enable	o/p
0/1	0	No
1	1	1
0	1	0

Active Low



Yp	Enable	o/p
0/1	1	No
1	0	1
0	0	0

FAYYAZ HUSSAIN

\* DAE Electronics (R.S.I.T)

\* B-Tech Electronics (P.U.I)